P-Channel Enhancement Mode Power MOSFET

Description

The G7P03LA uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

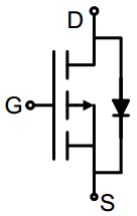
AEC-Q101 Qualified

General Features

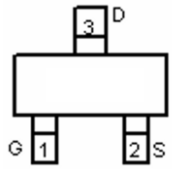
- V_{DS} -30V
- I_D (at V_{GS} = -10V) -7A
- $R_{DS(ON)}$ (at V_{GS} = -10V) < 23mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V) < 34mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

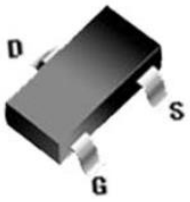
- Power switch
- DC/DC converters



Schematic diagram



Marking and pin assignment



SOT-23-3

Device	Package	Marking	Packaging
G7P03LA	SOT-23-3	G7P03	3000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Continuous Drain Current	I_D	-7	A
Pulsed Drain Current (note1)	I_{DM}	-28	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	1.9	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

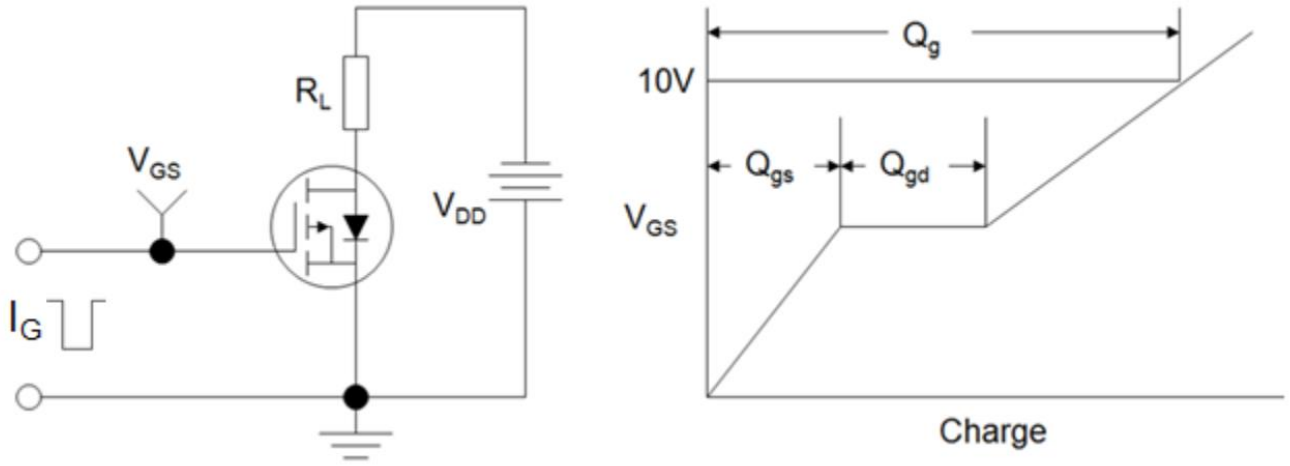
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	65.7	ºC/W

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V	--	--	-1	uA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = - 3A	--	19	23	mΩ
		V_{GS} = -4.5V, I_D = - 2A		27	34	
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz	--	1500	--	pF
Output Capacitance	C_{oss}		--	178	--	
Reverse Transfer Capacitance	C_{rss}		--	146	--	
Total Gate Charge	Q_g	V_{DD} = -15V, I_D = -6A, V_{GS} = -10V	--	29	--	nC
Gate-Source Charge	Q_{gs}		--	5.5	--	
Gate-Drain Charge	Q_{gd}		--	5.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -15V, I_D = -6A, R_G = 2.5Ω	--	10	--	ns
Turn-on Rise Time	t_r		--	44	--	
Turn-off Delay Time	$t_{d(off)}$		--	54	--	
Turn-off Fall Time	t_f		--	59	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-7	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -3A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Qrr	IS = -6A, V_{GS} = 0V di/dt=500A/us	--	6	--	nc
Reverse Recovery Time	trr		--	14	--	ns

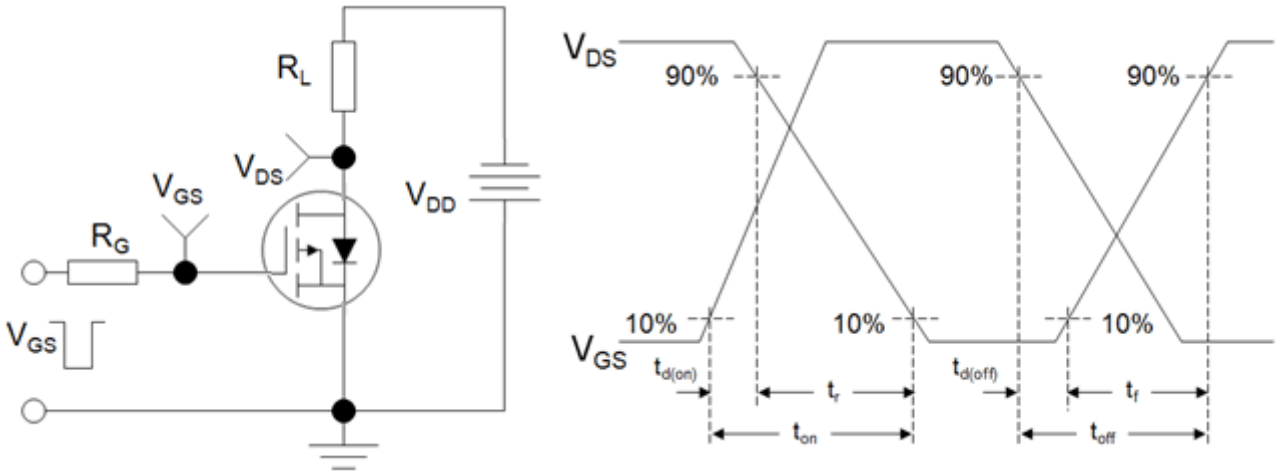
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

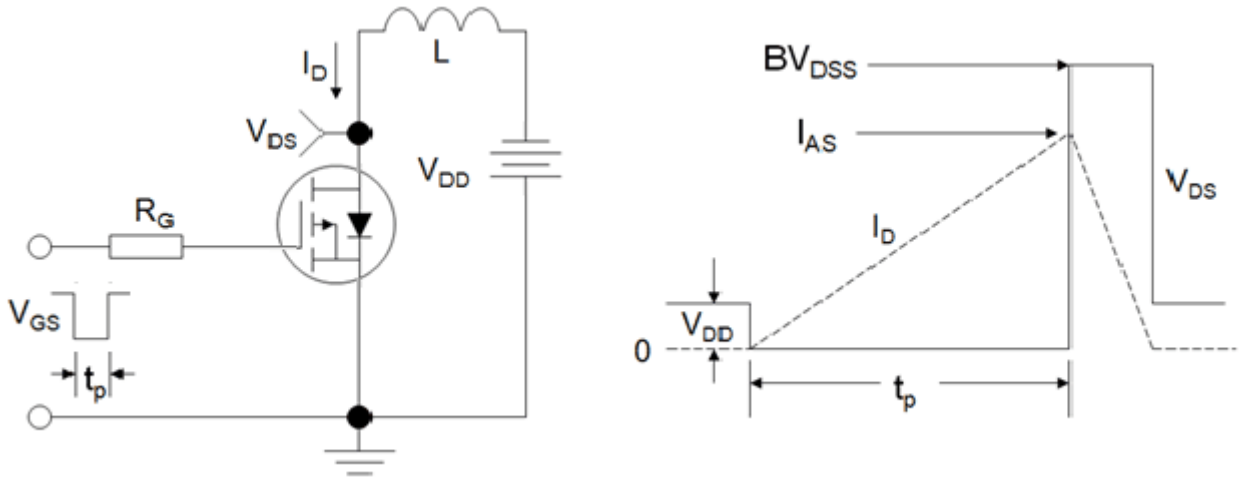
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

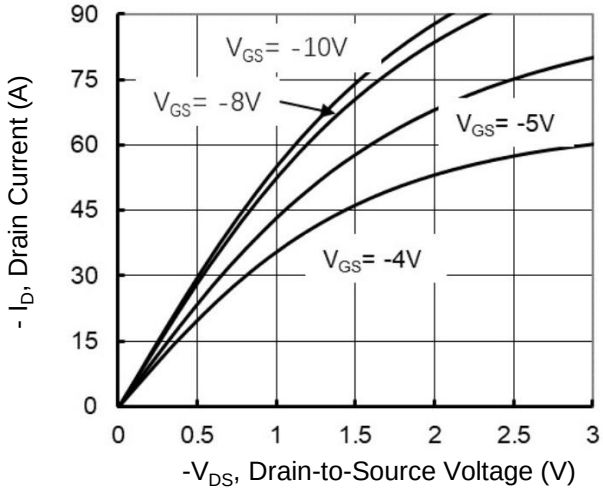


Figure 2. Transfer Characteristics

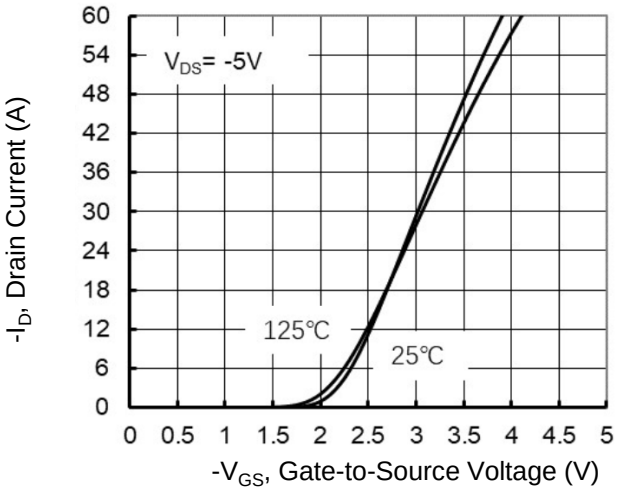


Figure 3. Gate Charge

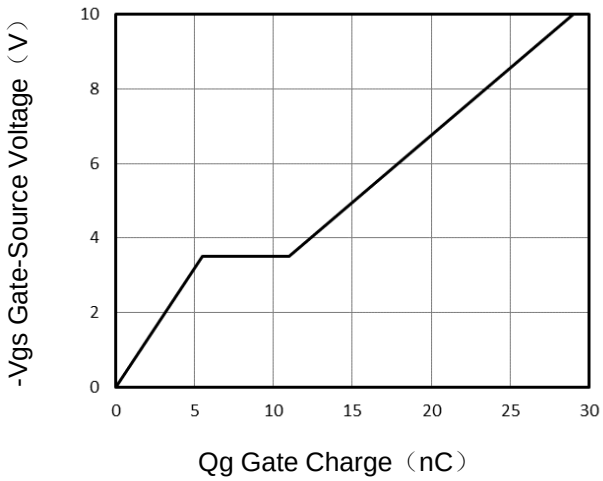


Figure 4. Drain Source On Resistance

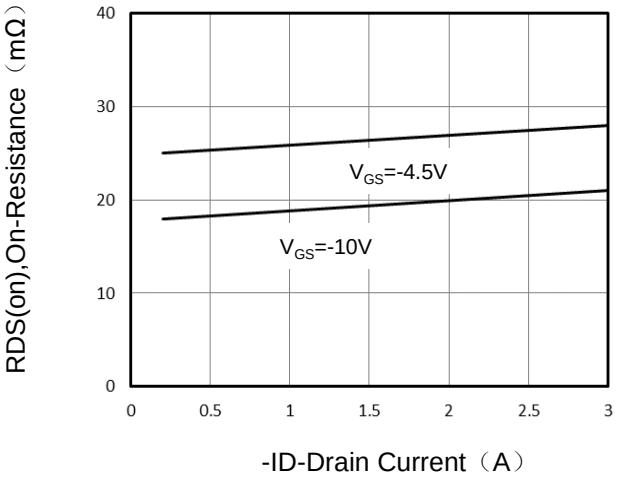


Figure 5. Capacitance

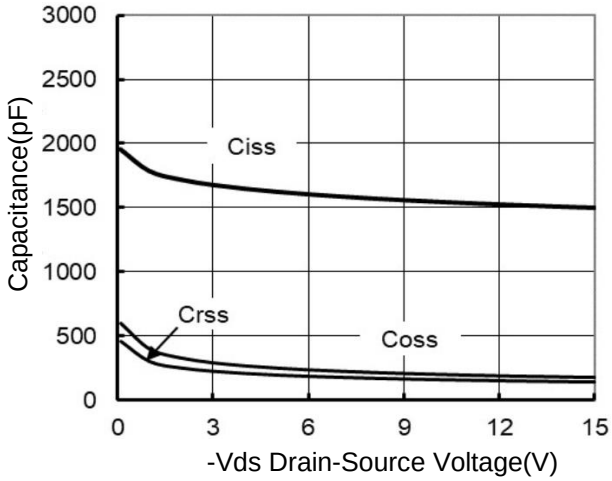
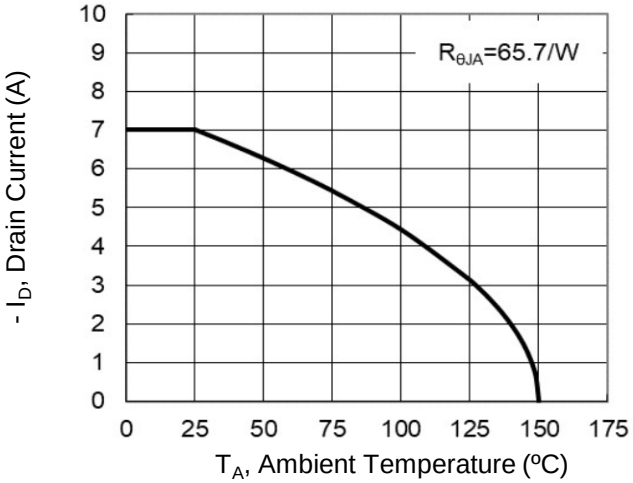


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

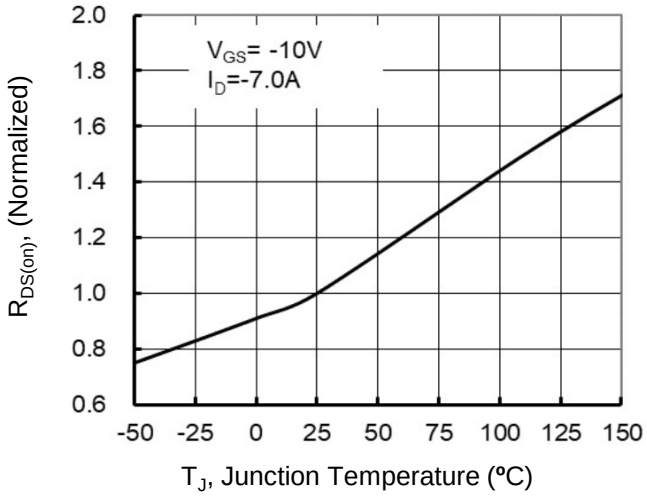


Figure 8. Safe Operation Area

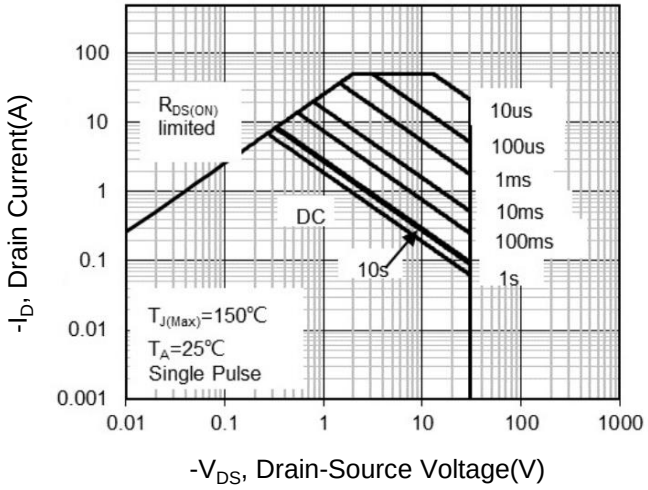
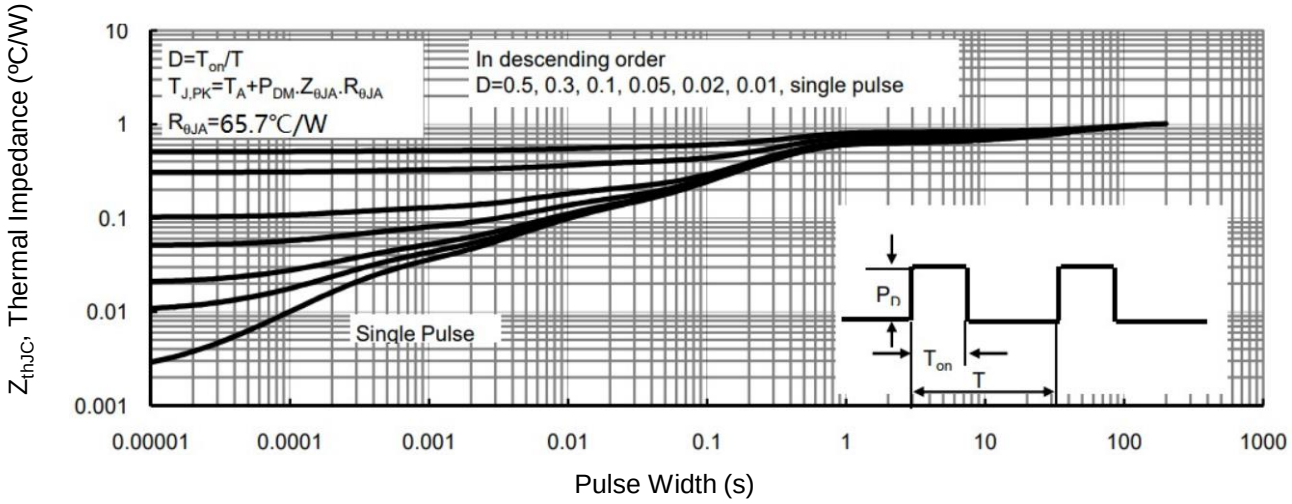
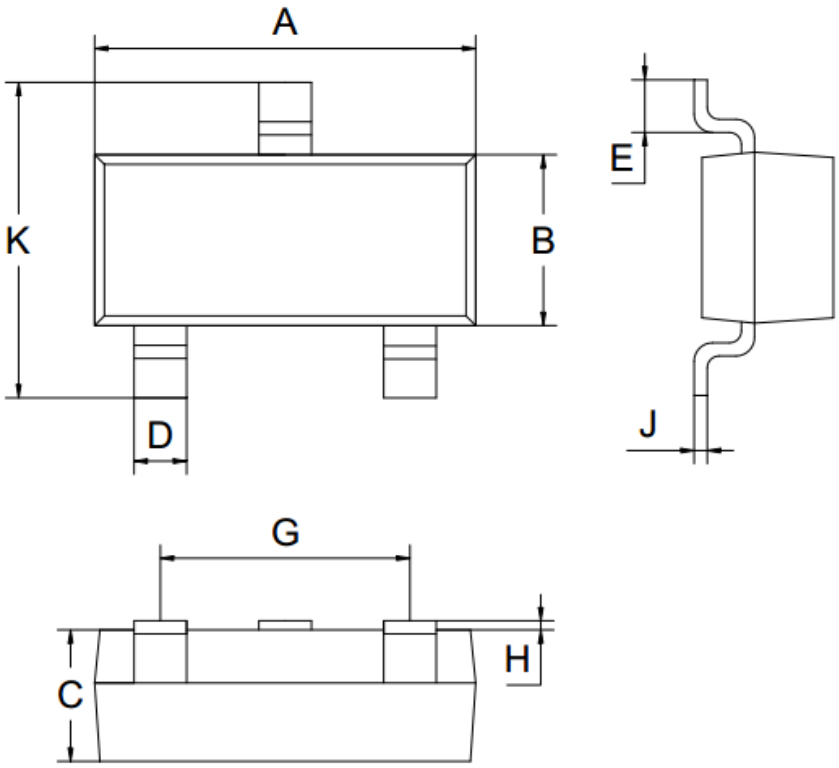


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-23-3 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.80	2.90	3.00
B	1.50	1.60	1.70
C	1.00	1.10	1.20
D	0.30	0.40	0.50
E	0.25	0.40	0.55
G	1.90		
H	0.00	-	0.10
J	0.047	0.127	0.207
K	2.60	2.80	3.00
All Dimensions in mm			